



Amendments to the Claims

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A semiconductor device comprising:

~~a substrate;~~a substrate having a first through-hole formed therein;

~~an electrode, the electrode~~an electrode being formed on the substrate;
~~the electrode having a second through-hole formed therein that overlaps with the first~~
~~through-hole, the second through-hole being larger than the first through-hole;~~

~~a through hole being formed through the electrode and the substrate in a~~
~~stacking direction of the electrode and the substrate, the through hole having a first diameter~~
~~in the substrate that is smaller than a second diameter in the electrode;~~

~~an interlayer dielectric being formed between the substrate and the electrode,~~
~~the interlayer dielectric having a third through-hole formed therein that overlaps with the first~~
~~and second through-holes, the third through-hole being larger than the first through-hole;~~

~~a conductive member being inserted into the through hole;~~first, second and
third through-holes, the conductive member having a first portion positioned in the first
through-hole and a second portion positioned in the second and third through-holes, the
second portion positioned in the second and third through-holes, the second portion having a
larger diameter than the first portion; and

~~an insulating material,~~material being disposed between the electrode
~~and around the conductive member,~~member in the first, second and third through-holes the
insulating material including a wall portion located higher than at least the electrode;
~~and electrode,~~

~~at least an interlayer dielectric being formed between the substrate and the~~
~~electrode, the through hole being formed in the interlayer dielectric, and surfaces of the~~

~~interlayer dielectric and substrate in the through hole being formed to have a level difference in a boundary area between the substrate and the interlayer dielectric,~~

the conductive member being formed over the wall portion of the insulating material from the first, second and third through-hole and being connected with the electrode.

2. (Currently Amended) The semiconductor device as defined in claim 1, wherein the insulating material is formed to cover an upper surface of the ~~electrode and a surface in the through hole,~~electrode, and includes a connection hole for connecting at least the electrode with the conductive member at a position differing from the ~~through hole,~~first, second and third through-holes, the wall portion being disposed between the connection hole and the ~~through hole-~~first, second and third through holes.

3-4. (Canceled)

5. (Original) The semiconductor device as defined in claim 1, wherein the conductive member functions as a connection terminal which secures electrical connection in an axial direction of the through-hole.

6. (Currently Amended) The semiconductor device as defined in claim 1, wherein a part of the conductive member projects outward from the ~~through-hole~~first, second and third through-holes on a side of the substrate opposite to a side on which the electrode is formed.

7. (Currently Amended) A semiconductor device comprising a plurality of the semiconductor devices as defined in claim 1 ~~which are~~which is stacked, each of the semiconductor devices being electrically connected through the conductive ~~members-~~member.

8. (Original) A circuit board comprising the semiconductor device as defined in claim 1.

9. (Original) An electronic instrument comprising the circuit board as defined in claim 8.

10-15. (Canceled)